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Docket No. 214438US0RD/in

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

IN RE APPLICATION OF: Masaaki ONOMURA, et al.

SERIAL NO: 09/964,463

GAU: 2811

FILED: September 28, 2001

EXAMINER:

FOR: SEMICONDUCTOR LASER DIODE

INFORMATION DISCLOSURE/RELATED CASE STATEMENT UNDER 37 CFR 1.97

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Applicant(s) wish to disclose the following information.

REFERENCES

- ☒ The applicant(s) wish to make of record the references listed on the attached form PTO-1449. Copies of the listed references are attached, where required, as are either statements of relevancy or any readily available English translations of pertinent portions of any non-English language references.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

RELATED CASES

- ☒ Attached is a list of applicant's pending application(s) or issued patent(s) which may be related to the present application. A copy of the patent(s), together with a copy of the claims and drawings of the pending application(s) is attached along with PTO 1449.
- ☐ A check is attached in the amount required under 37 CFR §1.17(p).

CERTIFICATION

- ☐ Each item of information contained in this information disclosure statement was first cited in any communication from a foreign patent office in a counterpart foreign application not more than three months prior to the filing of this statement.
- ☐ No item of information contained in this information disclosure statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to the knowledge of the undersigned, having made reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this statement.

DEPOSIT ACCOUNT

- ☒ Please charge any additional fees for the papers being filed herewith and for which no check is enclosed herewith, or credit any overpayment to deposit account number 15-0030. A duplicate copy of this sheet is enclosed.

Respectfully submitted,

OBLON, SPIVAK, McCLELLAND,
MAIER & NEUSTADT, P.C.


Norman F. Oblon
Registration No. 24,618

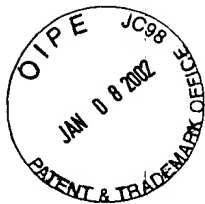


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LIST OF RELATED CASES

<u>Docket Number</u>	<u>Serial or Patent No.</u>	<u>Filing or Issue Date</u>	<u>Status or Patentee</u>
PER CLIENT	5,732,098	03/24/98	NISITANI, et al.
PER CLIENT	6,229,834	05/08/01	NISITANI, et al.

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DOCKET NO: 214438US0RD

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Group Art Unit: 2811

STATEMENT OF RELEVANCY

Reference AO (JP 09-219556) on Form 1449:

This reference discloses a nitride compound semiconductor laser comprising a multilayer structure including an n-type contact layer made of $\text{In}_x\text{Al}_y\text{Ga}_{1-x-y}\text{N}$ ($0 \leq x, 0 \leq y, x+y \leq 1$), a first n-type cladding layer including an aluminum, a second n-type cladding layer including an Indium, an activelayer, a first p-type cladding layer, a second p-type cladding layer, and a p-type contact layer.

Reference AP (JP 11-195840) on Form 1449:

This reference discloses a nitride compound semiconductor light emitting device comprising a multilayer structure including, at least, an n-type cladding layer consists of a super lattice structure including an aluminum.

Reference AQ (JP 11-238945) on Form 1449:

This reference discloses a nitride compound semiconductor light emitting device having an n-type cladding layer consists of a super lattice structure including Al, and a thickness of said n-type cladding layer (d) is more than $0.5\mu\text{m}$, and $d(\mu\text{m}) \times \chi_{\text{Al}}(\%) \geq 4.4$. (χ_{Al} ; a mean Aluminum composition in said n-type cladding layer).